

Silicon NPN Power Transistors

BD230

DESCRIPTION

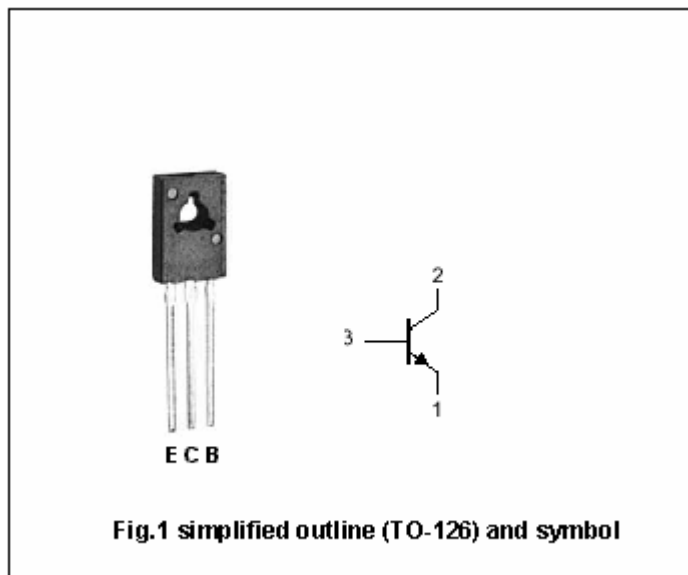
- With TO-126 package
- Complement to type BD231
- High current (Max:1.5A)
- Low voltage (Max: 80V)

APPLICATIONS

- Drive stage in TV circuits

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		1.5	A
I_{CM}	Collector current-Peak		3	A
I_{BM}	Base current-Peak		1	A
P_D	Total power dissipation	$T_{mb} \leq 62$	12.5	W
		$T_C=25$	10	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~150	
T_{amb}	Operating ambient temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.1A			0.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1A; I _B =0.1A			1.2	V
V _{BE}	Base-emitter on voltage	I _C =1A ; V _{CE} =2V			1.3	V
I _{CBO}	Collector cut-off current	V _{CB} =30V; I _E =0			0.1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	μ A
h _{FE-1}	DC current gain	I _C =5mA ; V _{CE} =2V	40			
h _{FE-2}	DC current gain	I _C =150mA ; V _{CE} =2V	40		250	
h _{FE-3}	DC current gain	I _C =1A ; V _{CE} =2V	25			
f _T	Transition frequency	I _C =50mA ; V _{CE} =5V		125		MHz

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PACKAGE OUTLINE

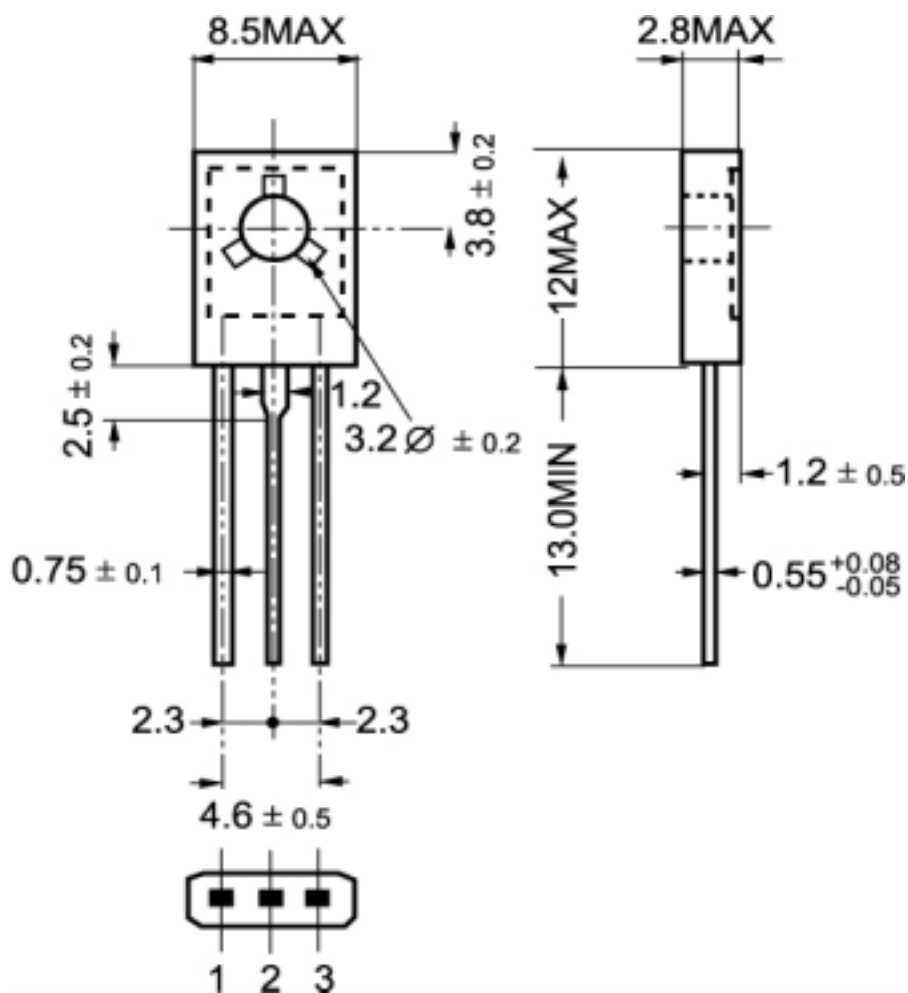


Fig.2 Outline dimensions